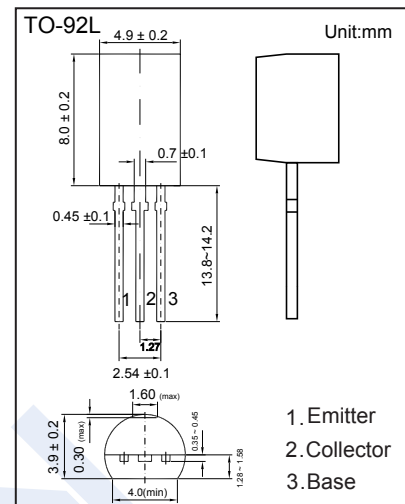


## PNP Transistors

## KTA1024

## ■ Features

- High Voltage and High  $f_T$
- Low Output Capacitance
- Complementary to KTC3206

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	-150	V
Collector - Emitter Voltage	$V_{CE0}$	-150	
Emitter - Base Voltage	$V_{EB0}$	-5	
Collector Current - Continuous	$I_C$	-50	mA
Emitter Current	$I_E$	50	
Collector Power Dissipation	$P_C$	1	W
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CB0}$	$I_C = -100 \mu\text{A}, I_E = 0$	-150			V
Collector- emitter breakdown voltage	$V_{CE0}$	$I_C = -1 \text{ mA}, I_B = 0$	-150			
Emitter - base breakdown voltage	$V_{EB0}$	$I_E = -100 \mu\text{A}, I_C = 0$	-5			
Collector-base cut-off current	$I_{CB0}$	$V_{CB} = -150 \text{ V}, I_E = 0$			-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EB0}$	$V_{EB} = -5 \text{ V}, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$			-0.8	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$			-1.2	
Base - emitter voltage	$V_{BE}$	$V_{CE} = -5 \text{ V}, I_C = -30 \text{ mA}$			-0.9	
DC current gain	$h_{FE}$	$V_{CE} = -5 \text{ V}, I_C = -10 \text{ mA}$	70		240	
Collector output capacitance	$C_{ob}$	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$			5	pF
Transition frequency	$f_T$	$V_{CE} = -30 \text{ V}, I_C = -10 \text{ mA}$		120		MHz

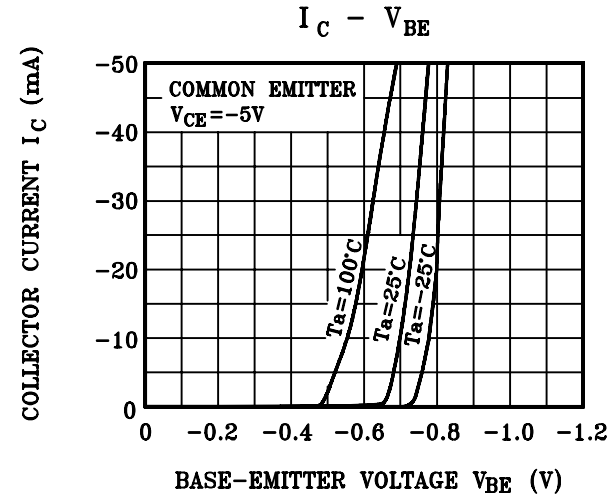
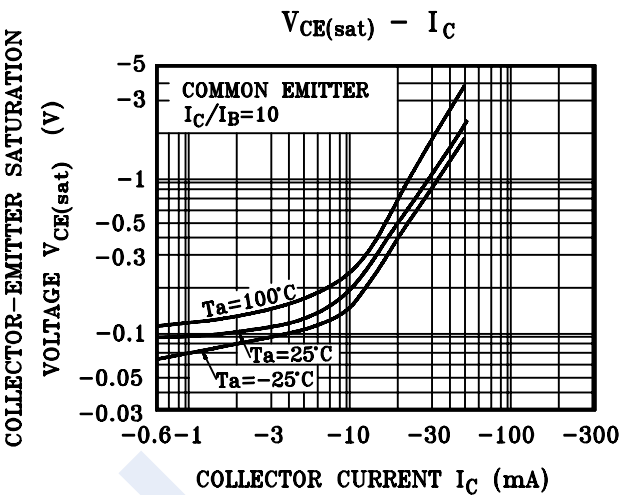
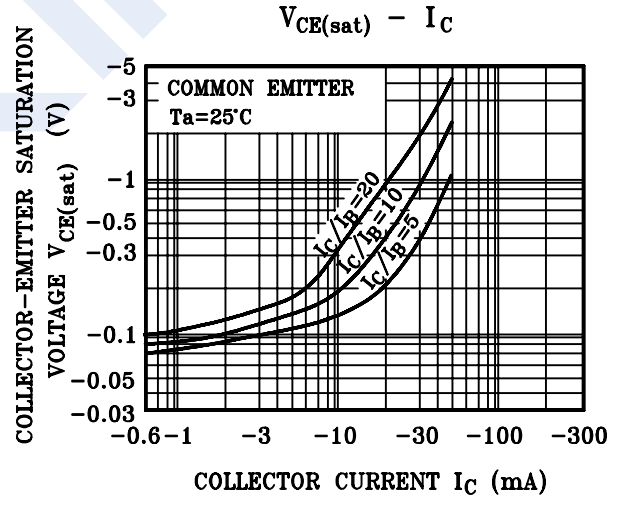
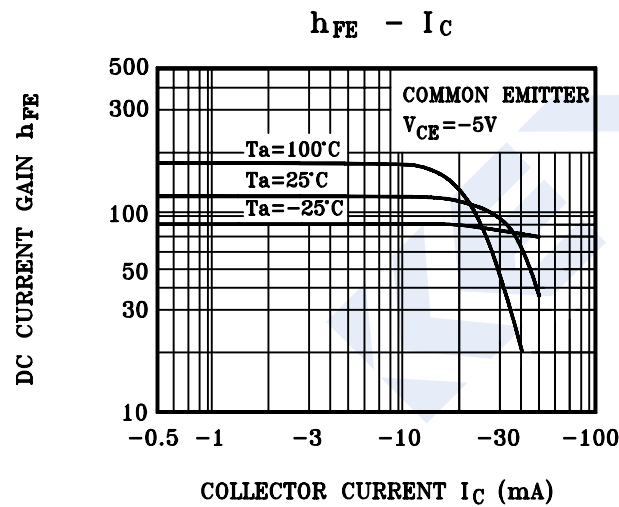
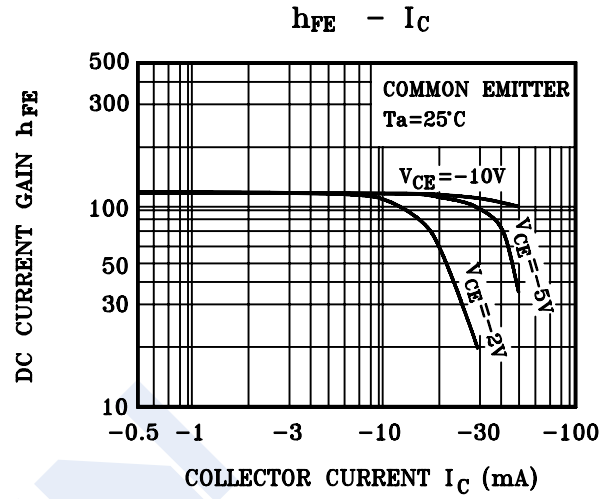
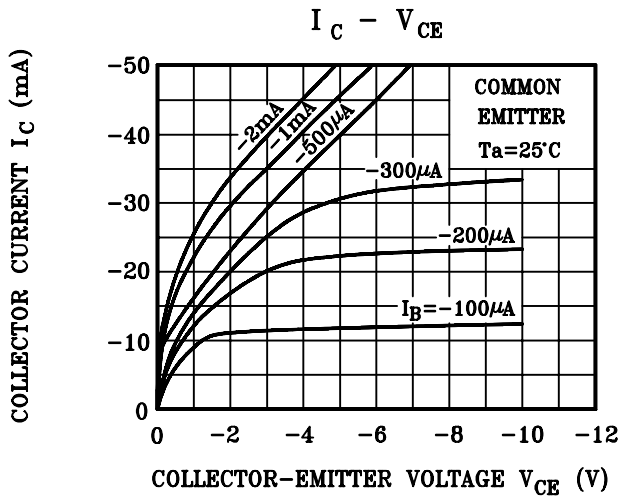
■ Classification of  $h_{FE}$ 

Type	KTA1024-O	KTA1024-Y
Range	70-140	120-240

# PNP Transistors

## KTA1024

■ Typical Characteristics



### PNP Transistors

### KTA1024

■ Typical Characteristics

